



www.china-base.com.hk

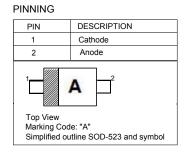
SOD-523

1SS355WT

Silicon Epitaxial Planar Switching

Features

- Small plastic package suitable
- for surface mounted design
- High reliability with high surge current handling capability



Applications

• High speed switching

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	90	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Peak Forward Current	I _{FM}	225	mA
Surge Forward Current (1 s)	I _{FSM}	500	mA
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Electrical Characteristics (Ta = 25 °C)

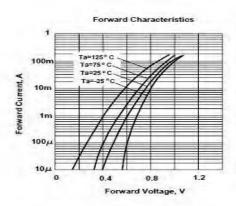
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	VF	1.2	V
Reverse Current at V _R = 80 V	I _R	0.1	μA
Capacitance between Terminals at V_R = 0.5 V, f = 1 MHz	Ст	3	pF
Reverse Recovery Time at V _R = 6 V, I _F = 10 mA, R _L = 100 Ω	t _{rr}	4	ns



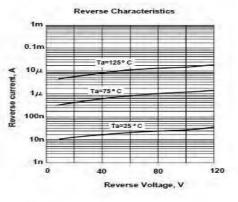




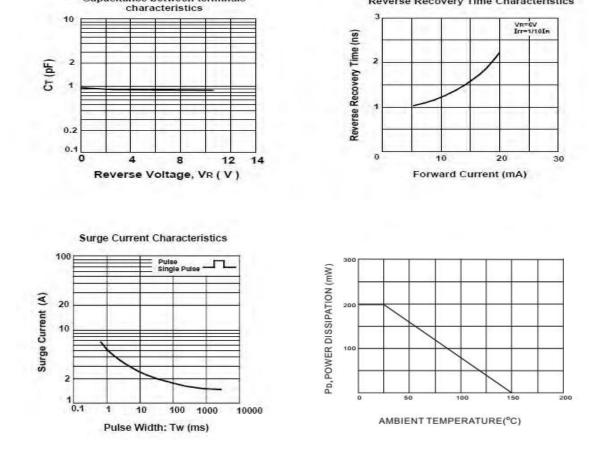
www.china-base.com.hk



Capacitance between terminals



Reverse Recovery Time Characteristics



Reverse Recovery Time Measurement Circuit

